

L Number	Hits	Search Text	DB	Time stamp
-	3	porous adj silicon and molecular adj switchable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:44
-	0	20030235927.URPN.	USPAT	2004/10/27 15:58
-	0	6788071.URPN.	USPAT	2004/10/27 16:04
-	0	6713339.URPN.	USPAT	2004/10/27 16:04
-	2	porous adj silicon and nano adj2 switch	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 16:06
-	7	10/304863	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 16:27
-	0	6806526.URPN.	USPAT	2004/10/27 16:29
-	15	(pores porous) near3 silicon and molecular adj (switch switchable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:43
-	6	((pores porous) near3 silicon and molecular adj (switch switchable)) not (porous adj silicon and molecular adj (switch switchable))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:05
-	71	(james near3 heath).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:05
-	1	(pores porous) near3 silicon and ((james near3 heath).in.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:19
-	128	(terry near3 gilton).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 10:58
-	16	((terry near3 gilton).in.) and porous adj (Si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 10:58
-	3	porous adj (Si semiconductor silicon) and molecular adj switchable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 11:51
-	108	(porous adj (Si semiconductor silicon) and memory) and (phase state) near2 change	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 11:51
-	3	porous adj silicon and (catenane rotaxane pseudorotaxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 16:37
-	692	porous adj (Si semiconductor silicon) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:42
-	19	(porous adj (Si semiconductor silicon) and memory) and redox	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:42
-	107	(porous adj silicon and memory) and (phase state) near2 change	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:43

	9	porous adj silicon and molecular adj (switch switchable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:43
	127	((pores porous) near2 (Si silicon) and memory) and (phase state) near2 change	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:44
	10	((porous adj (Si semiconductor silicon) and memory) and redox) not (((porous adj silicon and memory) and (phase state) near2 change) (porous adj silicon and molecular adj (switch switchable)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:44
	20	((pores porous) near2 (Si silicon) and memory) and (phase state) near2 change) not ((porous adj silicon and memory) and (phase state) near2 change)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:47
	136	(257/3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 15:04
	4	porous near3 (Si silicon) and (catenane rotaxane pseudorotaxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 13:40
	6	((365/151).CCLS.) and (pores porous) with (si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 16:58
	56	porous near3 (Si silicon) and memory same (switch switchable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 17:01
	120	(365/151).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 10:49
	10	((257/2).CCLS.) and (pores porous) near3 (si silicon semiconductor semiconductive)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 13:19
	90	redox and (catenane rotaxane pseudorotaxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 13:40
	61	(redox and (catenane rotaxane pseudorotaxane)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 14:15
	0	6756296.URPN.	USPAT	2004/10/29 14:45
	9	10/238880	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 07:57
	650	porous adj silicon and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:28
	64	porous adj silicon same memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:44
	128	(365/153).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:44
	1	((365/153).CCLS.) and (pore porous) near2 (si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:45

-	170	(257/2).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 14:47
-	589	(257/530).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 14:48
-	378	((257/530).CCLS.) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 14:48
-	104	((257/2).CCLS.) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 14:48